NTLJD3115P

MOSFET – Power, Dual, P-Channel, WDFN 2X2 mm
-20 V, -4.1 A

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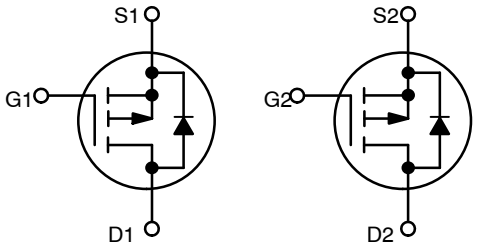
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX (Note 1)
−20 V	100 mΩ @ −4.5 V	−4.1 A
	135 mΩ @ −2.5 V	
	200 mΩ @ −1.8 V	

Features

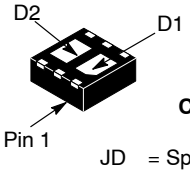
- WDFN Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- 2x2 mm Footprint Same as SC−88
- Lowest $R_{DS(on)}$ Solution in 2x2 mm Package
- 1.8 V $R_{DS(on)}$ Rating for Operation at Low Voltage Gate Drive Logic Level
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- Bidirectional Current Flow with Common Source Configuration
- This is a Pb−Free Device

Applications

- Optimized for Battery and Load Management Applications in Portable Equipment
- Li−Ion Battery Charging and Protection Circuits
- High Side Load Switch



P−CHANNEL MOSFET **P−CHANNEL MOSFET**



WDFN6
CASE 506AN

MARKING DIAGRAM



JD = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

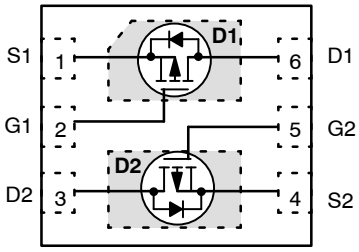
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−3.3	A
		T_A = 85°C		−2.4	
	t ≤ 5 s	T_A = 25°C		−4.1	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.5	W
	t ≤ 5 s			2.3	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	−2.3	A
		T_A = 85°C		−1.6	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.71	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−20	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode) (Note 2)			I_S	−1.9	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size of 30 mm^2, 2 oz Cu.

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

Device	Package	Shipping†
NTLJD3115PT1G	WDFN6 (Pb−Free)	3000/Tape & Reel
NTLJD3115PTAG	WDFN6 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
SINGLE OPERATION (SELF−HEATED)			
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	83	°C/W
Junction−to−Ambient − Steady State Min Pad (Note 4)	$R_{\theta JA}$	177	
Junction−to−Ambient − t ≤ 5 s (Note 3)	$R_{\theta JA}$	54	
DUAL OPERATION (EQUALLY HEATED)			
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	58	°C/W
Junction−to−Ambient − Steady State Min Pad (Note 4)	$R_{\theta JA}$	133	
Junction−to−Ambient − t ≤ 5 s (Note 3)	$R_{\theta JA}$	40	

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
4. Surface Mounted on FR4 Board using the minimum recommended pad size (30 mm^2, 2 oz Cu).

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−20			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = −250 μA, Ref to 25°C			9.95		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = −16 V, V_{GS} = 0 V	T_J = 25°C			−1.0	μA
			T_J = 85°C			−10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.4	−0.7	−1.0	V
Negative Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				2.44		mV/°C
Drain−to−Source On−Resistance	$R_{DS(on)}$	V_{GS} = −4.5, I_D = −2.0 A			75	100	mΩ
		V_{GS} = −2.5, I_D = −2.0 A			101	135	
		V_{GS} = −1.8, I_D = −1.6 A			150	200	
Forward Transconductance	g_{FS}	V_{DS} = −5.0 V, I_D = −2.0 A			6.0		S
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −10 V			531		pF
Output Capacitance	C_{OSS}				91		
Reverse Transfer Capacitance	C_{RSS}				56		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −10 V, I_D = −2.0 A			5.5	6.2	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.7		
Gate−to−Source Charge	Q_{GS}				1.0		
Gate−to−Drain Charge	Q_{GD}				1.4		
Gate Resistance	R_G				8.8		Ω
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −5.0 V, I_D = −1.0 A, R_G = 6.0 Ω			6.0		ns
Rise Time	t_r				11		
Turn−Off Delay Time	$t_{d(OFF)}$				21		
Fall Time	t_f				8.0		
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −10 V, I_D = −2.0 A, R_G = 2.0 Ω			6.0		ns
Rise Time	t_r				12		
Turn−Off Delay Time	$t_{d(OFF)}$				19		
Fall Time	t_f				6.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Recovery Voltage	V_{SD}	V_{GS} = 0 V, IS = −1.0 A	T_J = 25°C		−0.75	−1.0	V
			T_J = 125°C		−0.64		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, d_{ISD}/d_t = 100 A/μs, I_S = −1.0 A			12.6		ns
Charge Time	t_a				7.0		
Discharge Time	t_b				5.6		
Reverse Recovery Time	Q_{RR}				5.0		nC

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

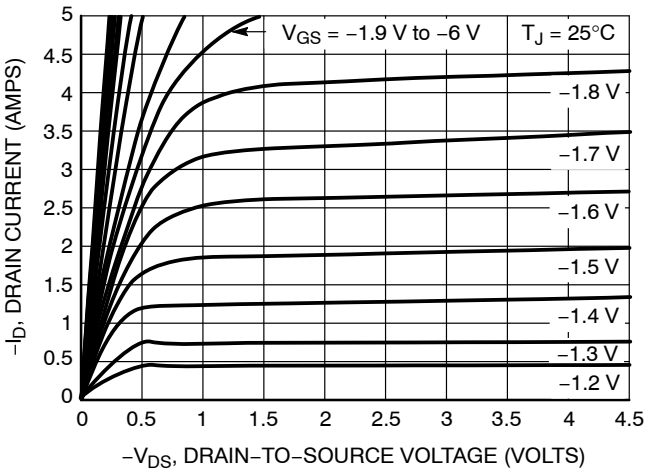


Figure 1. On−Region Characteristics

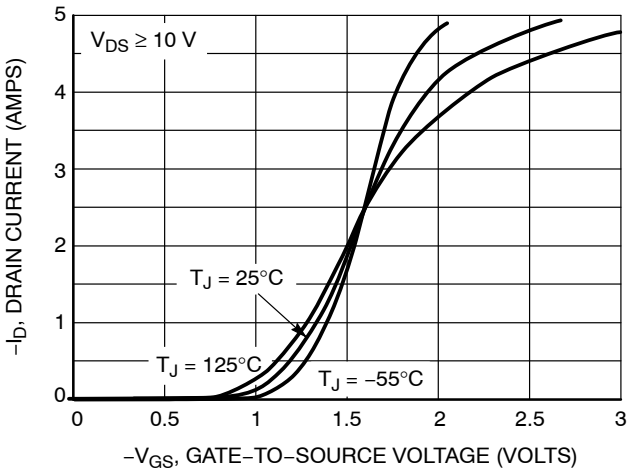


Figure 2. Transfer Characteristics

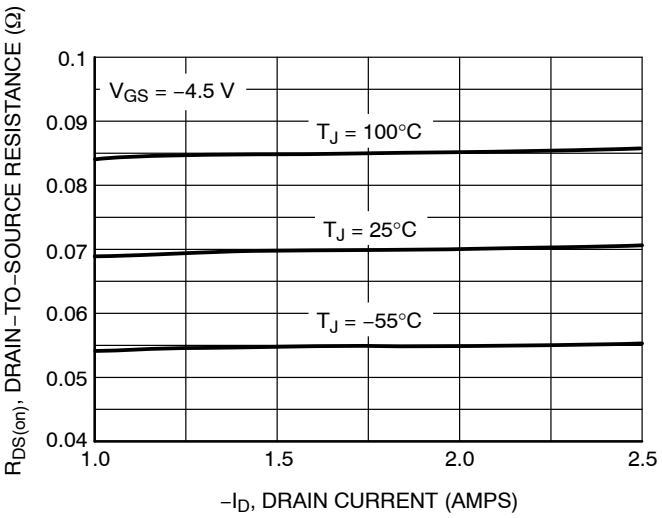


Figure 3. On−Resistance versus Drain Current

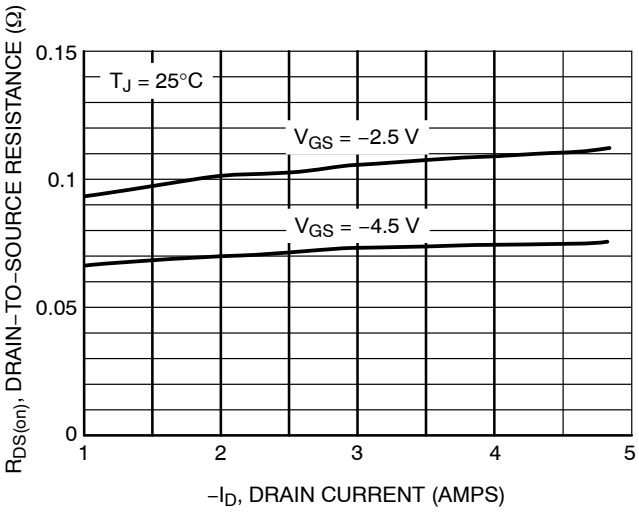


Figure 4. On−Resistance versus Drain Current and Gate Voltage

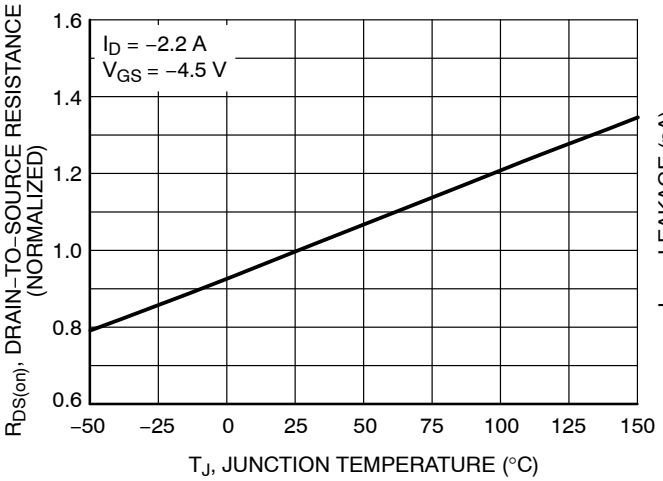


Figure 5. On−Resistance Variation with Temperature

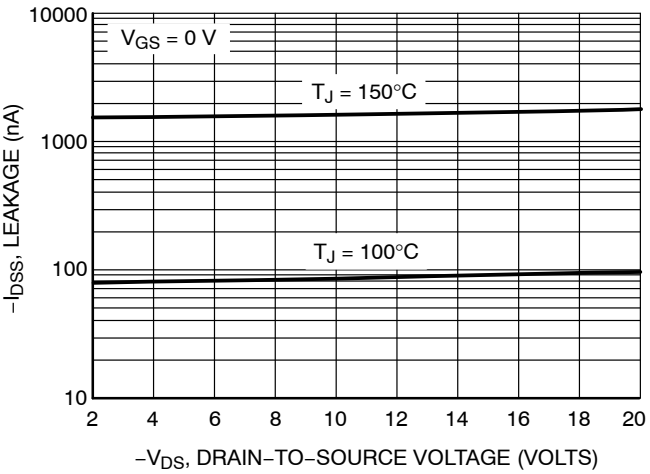


Figure 6. Drain−to−Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

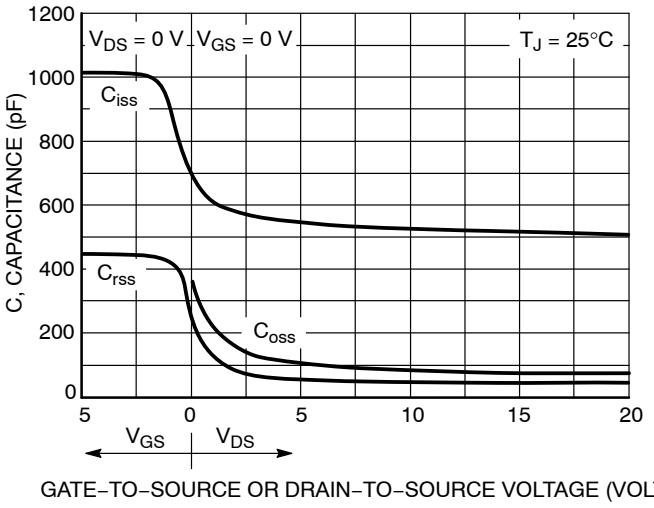


Figure 7. Capacitance Variation

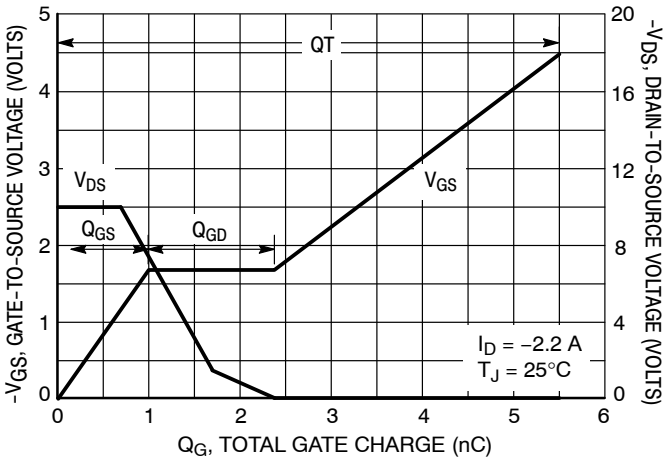


Figure 8. Gate−To−Source and Drain−To−Source Voltage versus Total Charge

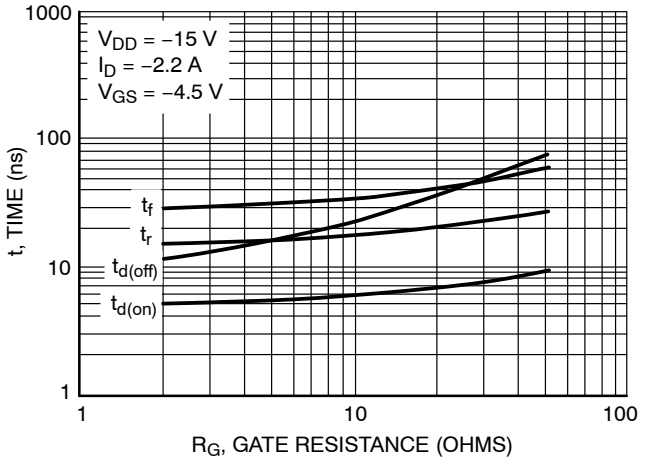


Figure 9. Resistive Switching Time Variation versus Gate Resistance

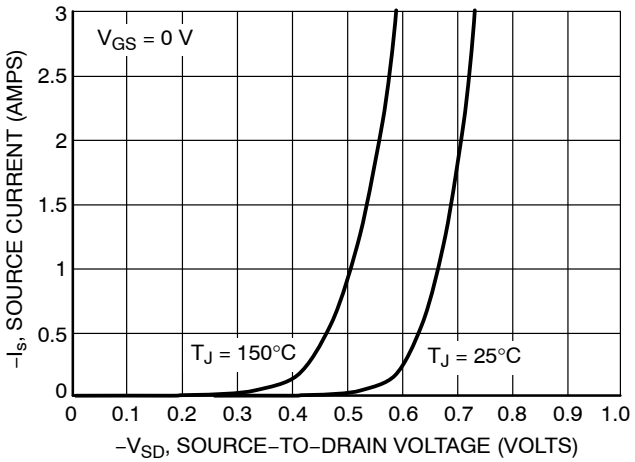


Figure 10. Diode Forward Voltage versus Current

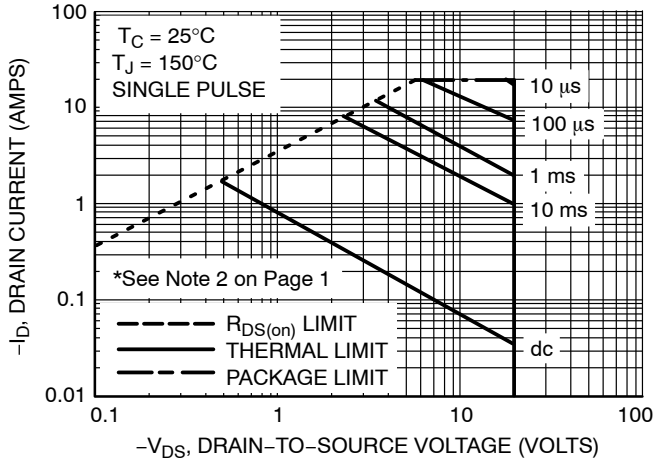


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

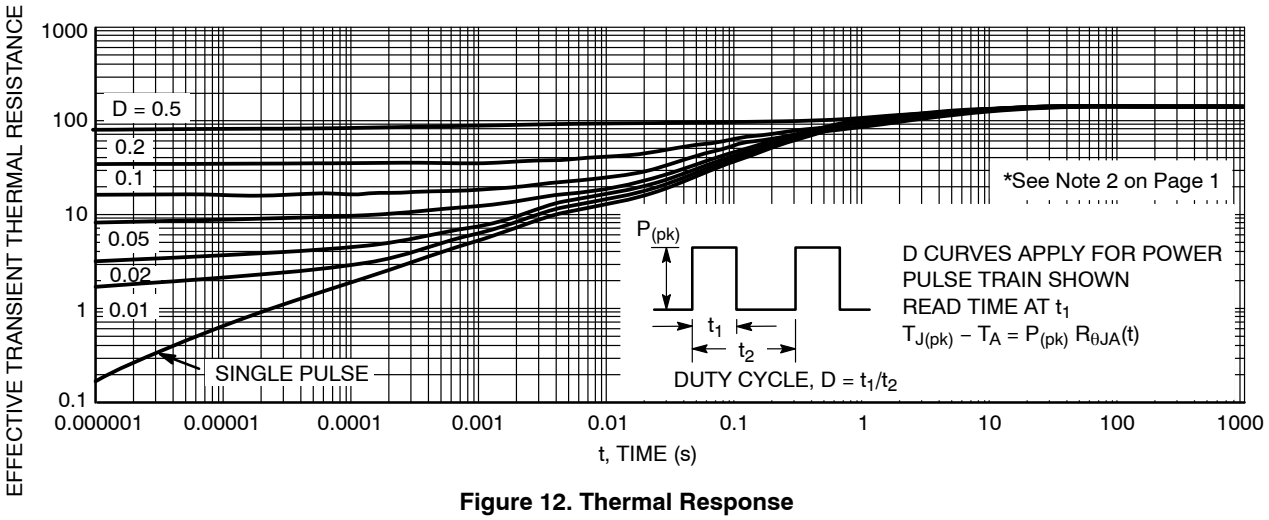
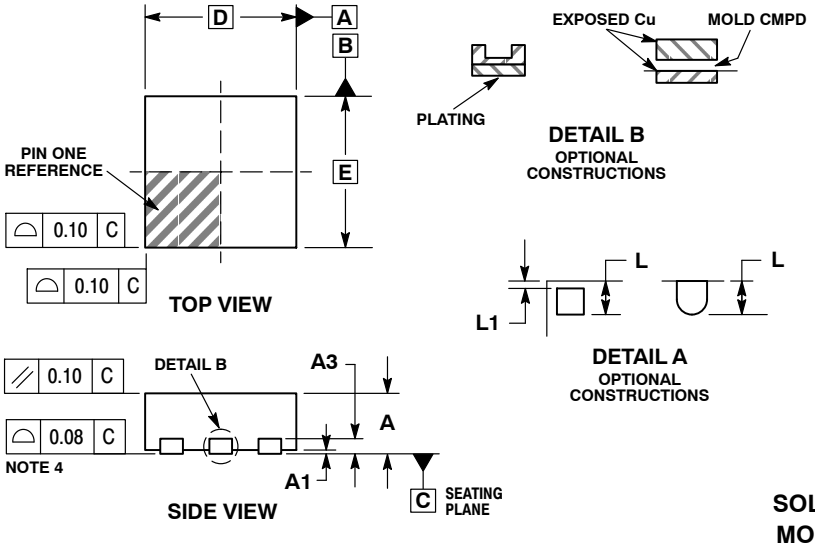


Figure 12. Thermal Response

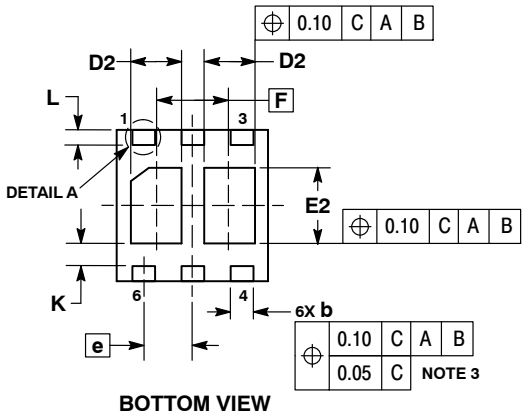
PACKAGE DIMENSIONS

WDFN6, 2x2
CASE 506AN
ISSUE G

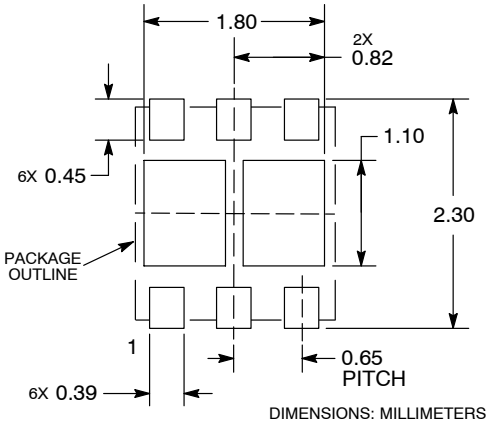


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
F	0.95 BSC	
K	0.25 REF	
L	0.20	0.30
L1	---	0.10



SOLDERMASK DEFINED MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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